

# Silicon PNP Epitaxial Planer Low Frequency Power Amplifier

REJ03G0482-0200 (Previous ADE-208-1387A (Z)) Rev.2.00 Dec.09.2004

#### **Features**

• Small size package: MPAK (SC–59A)

• Large Maximum current:  $I_C = -1$  A

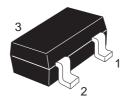
• Low collector to emitter saturation voltage:  $V_{CE(sat)} = -0.3 \text{ V max.} (\text{at } I_C/I_B = -0.5 \text{ A}/-0.05 \text{ A})$ 

• High power dissipation:  $P_C = 800 \text{ mW}$  (when using alumina ceramic board (25 x 60 x 0.7 mm))

• Complementary pair with 2SD2655

#### **Outline**

**MPAK** 



- 1. Emittei
- 2. Base
- 3. Collector

Note: Marking is "WL-".

## **Absolute Maximum Ratings**

 $(Ta = 25^{\circ}C)$ 

Item	Symbol	Ratings	Unit
Collector to base Voltage	$V_{CBO}$	-60	V
Collector to emitter voltage	$V_{\sf CEO}$	-50	V
Emitter to base voltage	$V_{EBO}$	-6	V
Collector current	Ic	-1	A
Collector peak current	ic(peak)	-2	A
Collector power dissipation	Pc	800*	mW
Junction temperature	Tj	150	°C
Storage temperature	Tstg	−55 to +150	°C

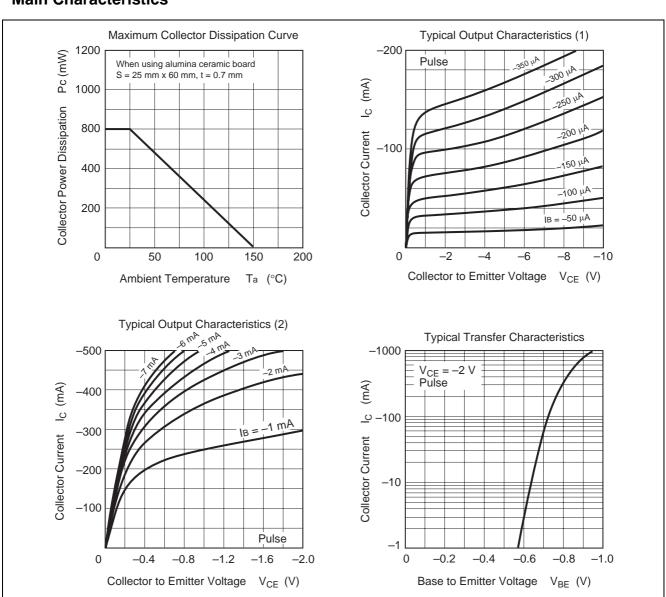
Note: \*When using alumina ceramic board (25 x 60 x 0.7 mm)

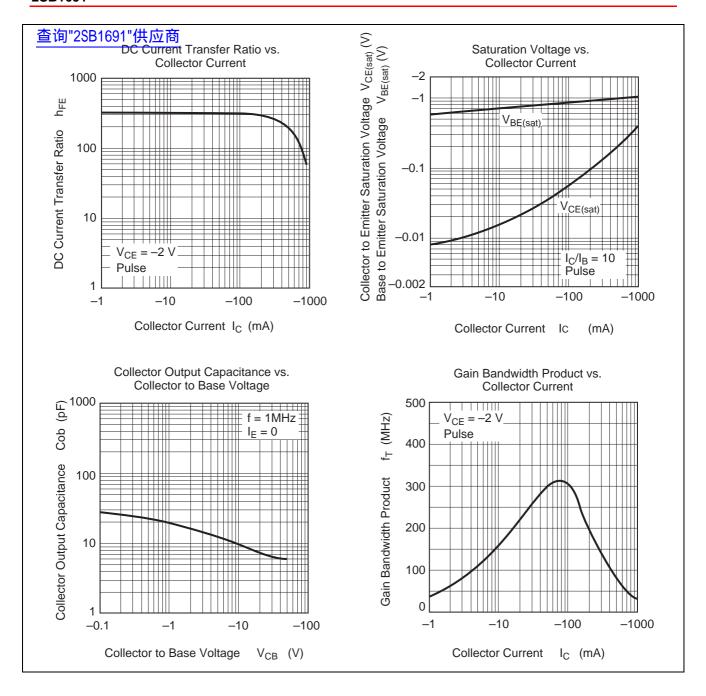
### Electrical (Characteristics

 $(Ta = 25^{\circ}C)$ 

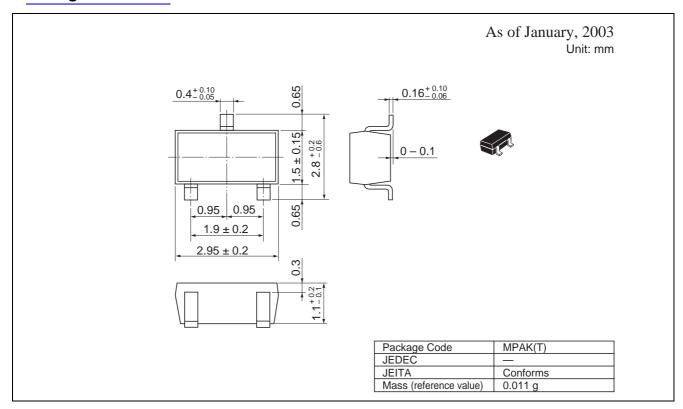
Item	Symbol	Min	Тур	Max	Unit	Test Condition
Collector to base breakdown voltage	$V_{(BR)CBO}$	-60	_	_	V	$I_C = -10 \mu\text{A}, \ I_E = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	-50	_	_	V	$I_C = -1 \text{ mA}, R_{BE} = \infty$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	-6	_		V	$I_E = -10 \ \mu A, \ I_C = 0$
Collector cutoff current	I <sub>CBO</sub>		_	-100	nA	$V_{CB} = -50 \text{ V}, I_E = 0$
Emitter cutoff current	I <sub>EBO</sub>		_	-100	nA	$V_{EB} = -5 \text{ V}, I_{C} = 0$
DC current transfer ratio	h <sub>FE</sub>	200	_	500		$V_{CE} = -2 \text{ V}, I_{C} = -0.1 \text{ A}$
Collector to emitter saturation voltage	V <sub>CE(sat)</sub>		-0.2	-0.3	٧	$I_{C} = -0.5 \text{ A}, I_{B} = -0.05 \text{ A},$ Pulse test
Base to emitter saturation voltage	$V_{BE(sat)}$	_	-0.95	-1.2	٧	$I_{C} = -0.5 \text{ A}, I_{B} = -0.05 \text{ A},$ Pulse test
Gain bandwidth product	f⊤	_	310	_	MHz	$V_{CE} = -2 \text{ V}, I_{C} = -0.1 \text{ A}$
Collector output capacitance	Cob	_	9.8	_	pF	$V_{CB} = -10 \text{ V}, I_E = 0,$ f = 1 MHz

#### **Main Characteristics**





# **Package 109mensions**



# **Ordering Information**

Part Name	Quantity	Shipping Container
2SB1691WL-	3000 pcs	φ178 mm Taping Reel

Note: For some grades, production may be terminated. Please contact the Renesas sales office to check the state of production before ordering the product.

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